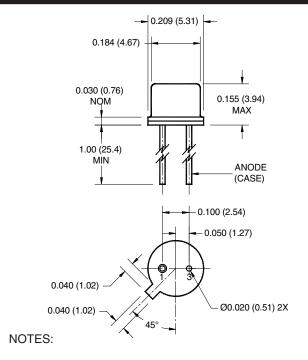


1N6265 GaAs INFRARED EMITTING DIODE

PACKAGE DIMENSIONS



- 1. Dimensions for all drawings are in inches (mm).
- 2. Tolerance of \pm .010 (.25) on all non-nominal dimensions unless otherwise specified.

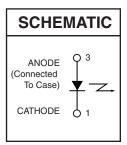
FEATURES

- · Good optical to mechanical alignment
- Mechanically and wavelength matched to the TO-18 series phototransistor
- · Hermetically sealed package
- High irradiance level
- (*) Indicates JEDEC registered values

DESCRIPTION

• The 1N6265 is a 940 nm LED in a narrow angle, TO-46 package.





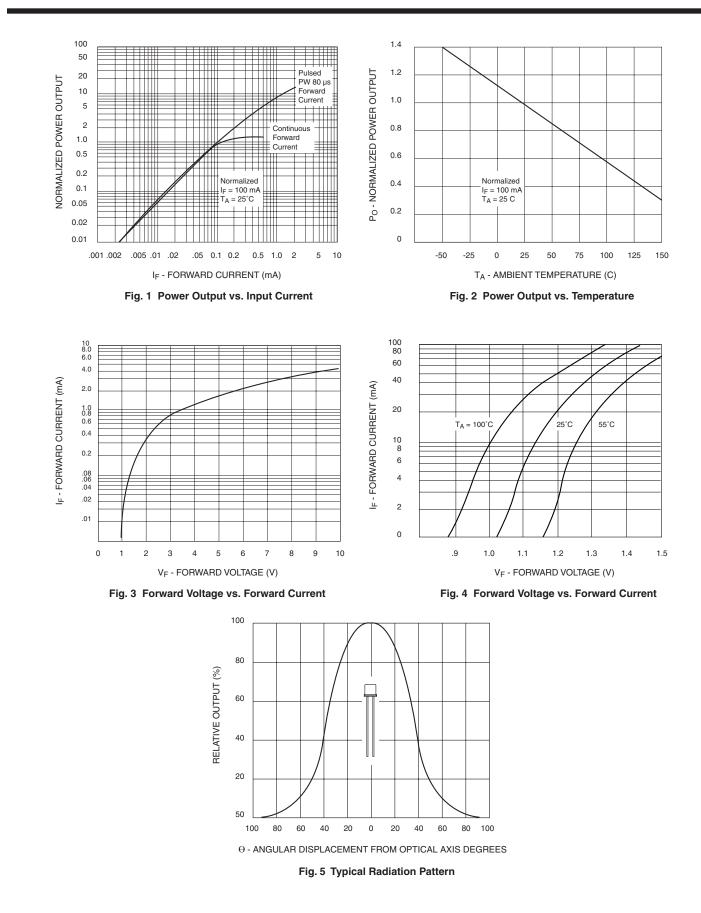
- 1. Derate power dissipation linearly 1.70 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 13.0 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension
- 7. Total power output, P_0 , is the total power radiated by the device into a solid angle of 2 π steradians.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified) Symbol Unit Parameter Rating **Operating Temperature** -65 to +125 °C T_{OPR} °C *Storage Temperature -65 to +150 TSTG *Soldering Temperature (Iron)(3,4,5 and 6) 240 for 5 sec °C T_{SOL-I} *Soldering Temperature (Flow)(3,4 and 6) 260 for 10 sec °C T_{SOL-F} *Continuous Forward Current 100 mΑ I_{F} *Forward Current (pw, 1µs; 200Hz) 10 $|_{F}$ А V *Reverse Voltage V_{R} 3 *Power Dissipation $(T_A = 25^{\circ}C)^{(1)}$ 170 mW P_D P_D Power Dissipation $(T_C = 25^{\circ}C)^{(2)}$ 1.3 W

ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNITS
*Peak Emission Wavelength	I _F = 100 mA	λ_{PE}	935	—	955	nm
Emission Angle at 1/2 Power		θ	_	±40	—	Deg.
*Forward Voltage	I _F = 100 mA	V _F	_	_	1.7	V
*Reverse Leakage Current	V _R = 3 V	I _R	_	_	10	μA
*Total Power	I _F = 100 mA	Po	6	_	—	mW
Rise Time 0-90% of output		t _r	_	1.0	—	μs
Fall Time 100-10% of output		t _f	—	1.0	—	μs

1N6265 GaAs INFRARED EMITTING DIODE



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1N6265 GaAs INFRARED EMITTING DIODE

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